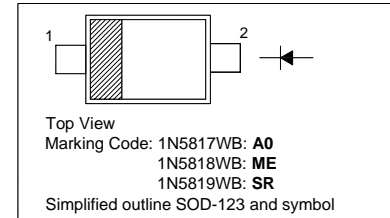


1N5817WB-1N5819WB

1 A SURFACE MOUNT SCHOTTKY BARRIER DIODE

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

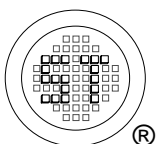


Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	1N5817WB	20
		1N5818WB	30
		1N5819WB	40
Average Forward Rectified Current	I_O	1	A
Non-Repetitive Peak Forward Surge Current (8.3 ms Single Half Sine-Wave)	I_{FSM}	25	A
Power Dissipation	P_{tot}	450	mW
Operating Temperature Range	T_j	- 55 to + 150	$^\circ\text{C}$
Storage Temperature Range	T_s	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 1\text{ mA}$	V_{BR}	1N5817WB	20	-
		1N5818WB	30	-
		1N5819WB	40	-
Reverse Voltage Leakage Current at $V_R = 20\text{ V}$ at $V_R = 30\text{ V}$ at $V_R = 40\text{ V}$ at $V_R = 4\text{ V}$ at $V_R = 6\text{ V}$	I_R	1N5817WB	-	1
		1N5818WB	-	1
		1N5819WB	-	1
		1N5819WB	-	0.05
		1N5819WB	-	0.075
Forward Voltage at $I_F = 0.1\text{ A}$ at $I_F = 1\text{ A}$ at $I_F = 3\text{ A}$	V_F	1N5819WB	-	0.45
		1N5817WB	-	0.45
		1N5818WB	-	0.55
		1N5819WB	-	0.6
		1N5817WB	-	0.75
		1N5818WB	-	0.875
1N5819WB	-	0.9		
Diode Capacitance at $V_R = 4\text{ V}$, $f = 1\text{ MHz}$	C_D	-	120	pF



SEMTECH ELECTRONICS LTD.

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ISO/TS 16949 : 2002
Certificate No. 05103



ISO 14001:2004
Certificate No. 71116



ISO 9001:2000
Certificate No. 0506098

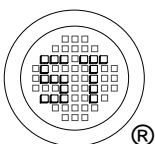
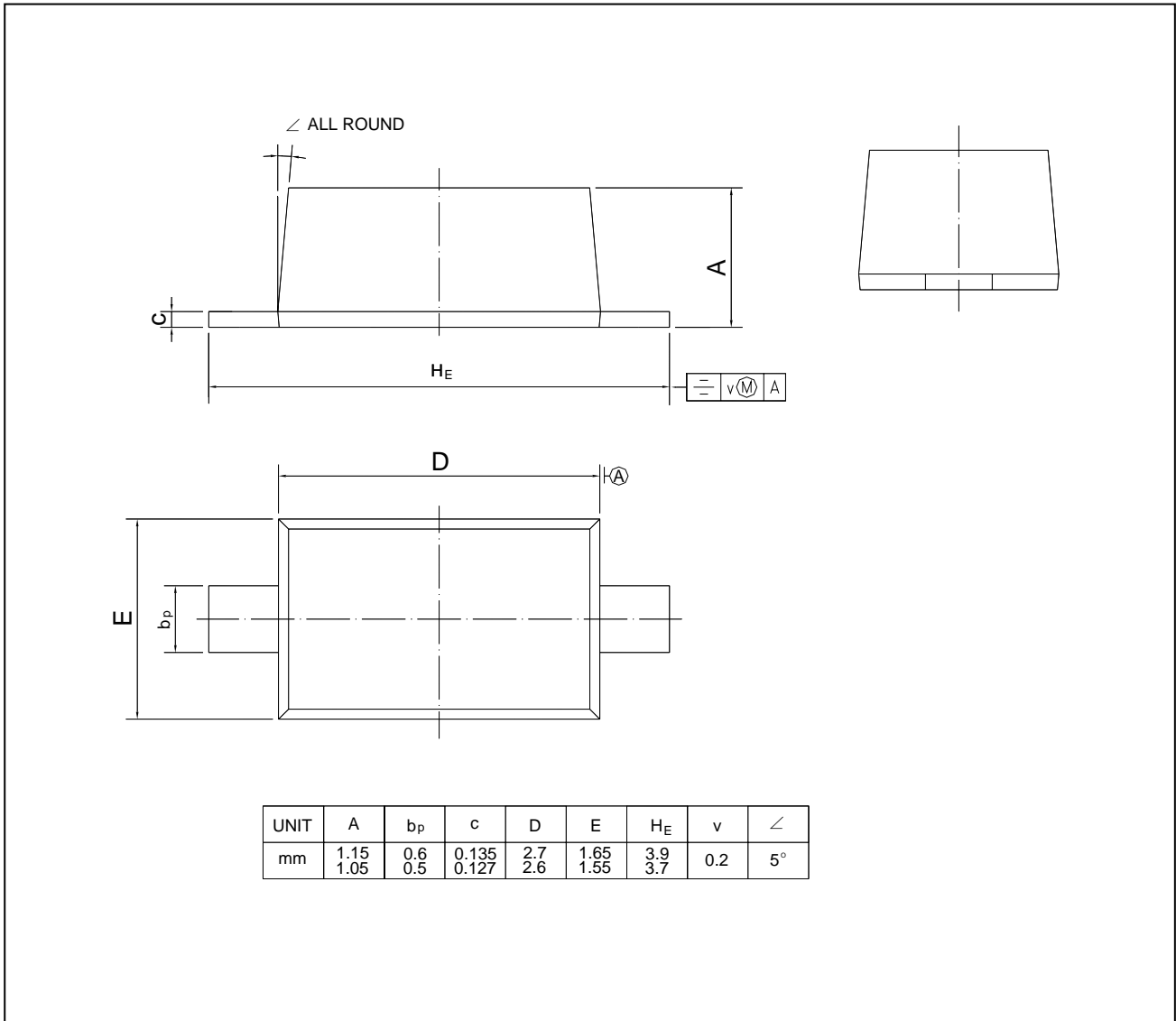
Dated : 20/12/2006

1N5817WB-1N5819WB

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-123



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